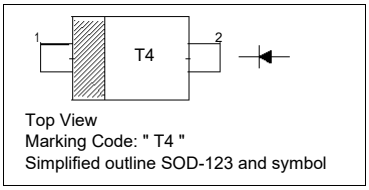
1N4148W Silicon Epitaxial Planar Switching Diode

Features

• Fast switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: " T4 "
Simplified outline SOD-123 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current at t = 1 μs	I_{FSM}	2	A
Power Dissipation	P_{tot}	400	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50 mA at I_F = 150 mA	V_F	 - - - -	 0.715 0.855 1 1.25	 V
Peak Reverse Current at V_R = 75 V at V_R = 20 V at V_R = 75 V, T_J = 150 °C at V_R = 25 V, T_J = 150 °C	I_R	 - - - -	 1 25 50 30	 μA nA μA μA
Total Capacitance at V_R = 0 V, f = 1 MHz	C_T	-	2	pF
Reverse Recovery Time at I_{rr} = 0.1 X I_R, I_F = I_R = 10 mA, R_L = 100 Ω	t_{rr}	-	4	ns

Typical Characteristics

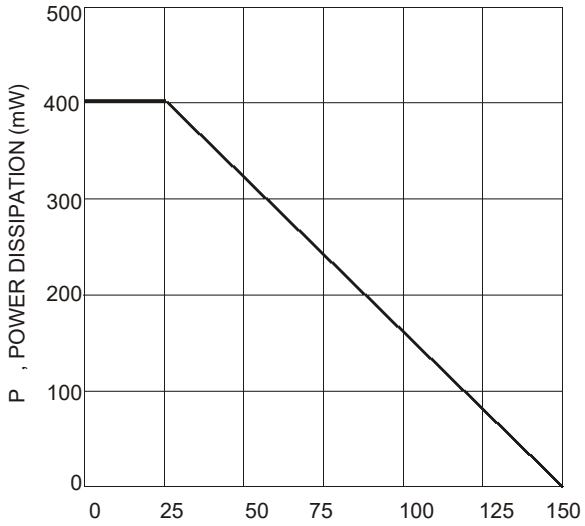


Fig. 1 Power Derating Curve

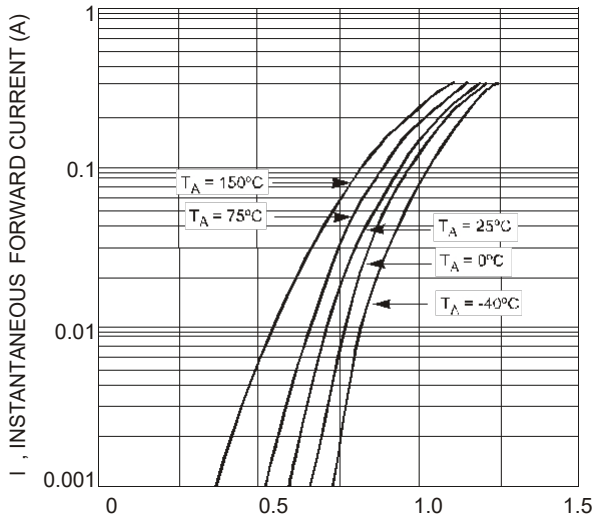


Fig. 2 Typical Forward Characteristics

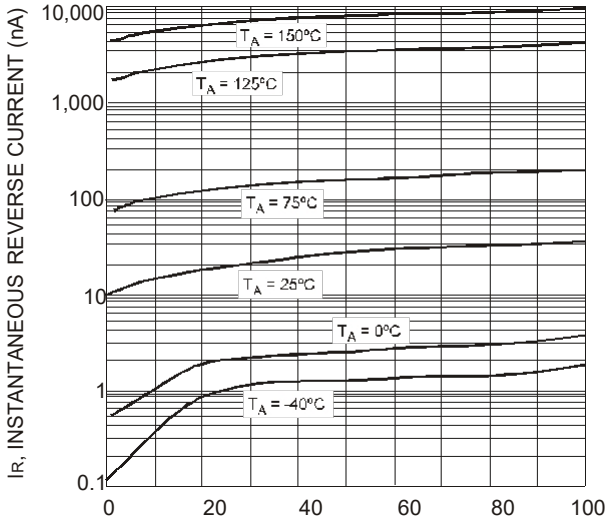


Fig. 3 Typical Reverse Characteristics

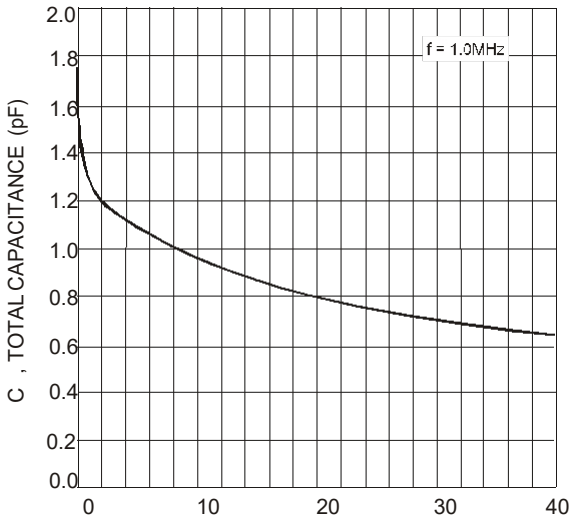
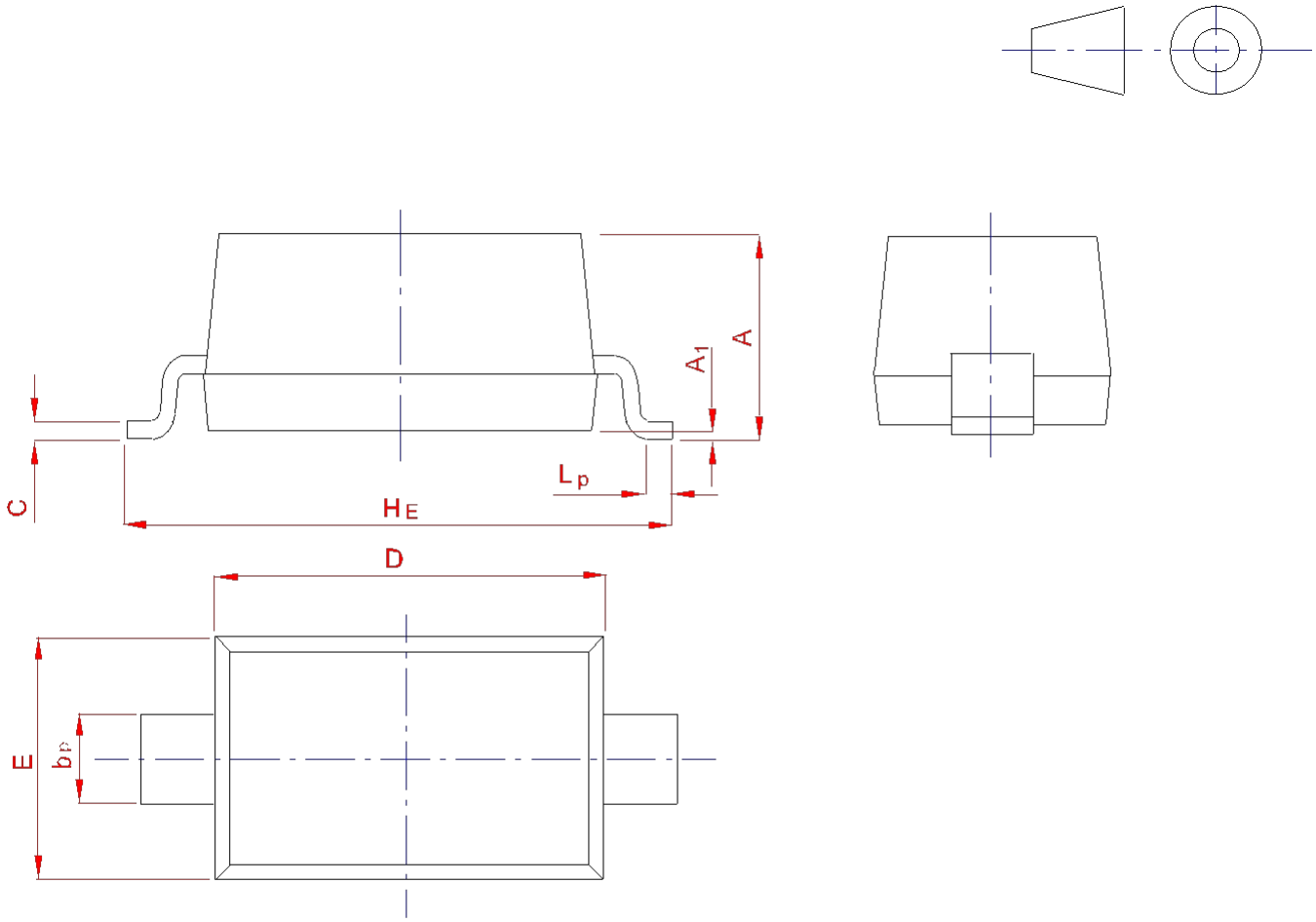


Fig. 4 Total Capacitance vs. Reverse Voltage

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-123**



UNIT	A	b_p	C	D	E	H_E	A_1	L_p
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20